

CLAIMS

1. For semiconductor manufacturing equipment, a ceramic susceptor having a resistive heating element on a surface of or inside a ceramic substrate,
5 the ceramic susceptor for semiconductor manufacturing equipment characterized in that the smallest angle formed by the bottom face and lateral faces of the resistive heating element in section is 5° or greater.

2. A ceramic susceptor for semiconductor manufacturing equipment as set forth in claim 1, characterized in that when a wafer is placed on the wafer support
10 surface and the resistive heating element is drawing current and heated deviation in the wafer surface temperature is $\pm 1.0\%$ or less at working temperature.

3. A ceramic susceptor for semiconductor manufacturing equipment as set forth in claim 2, characterized in that deviation in the wafer surface temperature is within $\pm 0.5\%$ at working temperature.

15 4. A ceramic susceptor for semiconductor manufacturing equipment as set forth in any of claims 1 to 3, characterized in that the ceramic substrate is made of at least one ceramic selected from aluminum nitride, silicon nitride, aluminum oxynitride and silicon carbide.

5. A ceramic susceptor for semiconductor manufacturing equipment as set
20 forth in any of claims 1 to 4, characterized in that the ceramic substrate is either aluminum nitride or silicon carbide of $100 \text{ W/m}\cdot\text{K}$ or greater thermal conductivity.

6. A ceramic susceptor for semiconductor manufacturing equipment as set forth in any of claims 1 to 5, characterized in that the resistive heating element is

made from at least one metal selected from tungsten, molybdenum, platinum, palladium, silver, nickel and chrome.

7. A ceramic susceptor for semiconductor manufacturing equipment as set forth in any of claims 1 to 4, characterized in that further a plasma electrode is
- 5 disposed on a surface of or inside the ceramic substrate.